

## UNITED STATES PATENT AND TRADEMARK OFFICE

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER OF PATENTS AND TRADEMARKS Washington, D.C. 20231 www.uspto.gov

APPLICATION NO.	F	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/004,168		10/30/2001	Makoto Ono	16869P-037300US	300US 8661	
20350	7590	04/01/2003				
		TOWNSEND AN	EXAMINER			
TWO EMBARCADERO CENTER EIGHTH FLOOR SAN FRANCISCO. CA 94111-3834				WHITMORE, STAC		
5.11.110111	c.500, C	71 74111-303 <del>4</del>		ART UNIT	PAPER NUMBER	
				2812		

DATE MAILED: 04/01/2003

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application No.	Applicant(s)	
4.	•	10/004,168	ONO ET AL.	,
•	Office Action Summary	Examiner	Art Unit	
•		Stacy A Whitmore		
	The MAILING DATE of this communication ap		eet with the correspondence address -	
Period fo	or Reply	, , , , , , , , , , , , , , , , , , ,	eet was the correspondence address -	-
THE I - Exter after - If the - If NO - Failu - Any r	ORTENED STATUTORY PERIOD FOR REPL MAILING DATE OF THIS COMMUNICATION. nsions of time may be available under the provisions of 37 CFR 1. SIX (6) MONTHS from the mailing date of this communication. period for reply specified above is less than thirty (30) days, a reply period for reply is specified above, the maximum statutory period re to reply within the set or extended period for reply will, by statutely received by the Office later than three months after the mailined patent term adjustment. See 37 CFR 1.704(b).	136(a). In no event, however	may a reply be timely filed  n of thirty (30) days will be considered timely.  (6) MONTHS from the mailing date of this communications and the second	ation.
1)⊠	Responsive to communication(s) filed on 30	October 2001 .		
2a) <u></u> □		his action is non-final		
3) <u>□</u> Dispositi	Since this application is in condition for allow closed in accordance with the practice under on of Claims	rance except for form Ex parte Quayle, 19	al matters, prosecution as to the merit 35 C.D. 11, 453 O.G. 213.	ts is
4) 🖾	Claim(s) 21,27,28,31 and 36-38 is/are pendir	ng in the application.		
	4a) Of the above claim(s) is/are withdra	wn from consideration	n.	
5) 🗌	Claim(s) is/are allowed.			
6)⊠	Claim(s) 21,27,28,31 and 36-38 is/are rejected	d.		
7)	Claim(s) is/are objected to.			
	Claim(s) are subject to restriction and/o	or election requireme	nt	
Application	on Papers			
9) 🗌 🗆	The specification is objected to by the Examine	er.		
10)⊠ 1	Γhe drawing(s) filed on <u>30 <i>October 2001</i></u> is/are	∶ a) accepted or b)	objected to by the Examiner.	
	Applicant may not request that any objection to the	e drawing(s) be held in	abeyance. See 37 CFR 1.85(a).	
11)[] 7	The proposed drawing correction filed on		) disapproved by the Examiner.	
🗖 -	If approved, corrected drawings are required in re	•		
	The oath or declaration is objected to by the Ex	kaminer.		
Priority u	nder 35 U.S.C. §§ 119 and 120			
13)⊠	Acknowledgment is made of a claim for foreig	n priority under 35 U.	S.C. § 119(a)-(d) or (f).	
a)[	☑ All b) ☐ Some * c) ☐ None of:			
	1. Certified copies of the priority document	ts have been receive	d.	
,	<ol><li>Certified copies of the priority document</li></ol>	ts have been receive	d in Application No	
	<ol> <li>Copies of the certified copies of the prio application from the International Bu ee the attached detailed Office action for a list</li> </ol>	ireau (PCT Rule 17.2	(a)).	
	cknowledgment is made of a claim for domest	·		ation).
a)	☐ The translation of the foreign language procedures the company of the foreign language procedures the company of the compan	ovisional application	nas been received.	<b></b>
Attachment			• •	
2) Notice 3) Inform	e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-948) nation Disclosure Statement(s) (PTO-1449) Paper No(s) 3	5) □ No	rview Summary (PTO-413) Paper No(s) ice of Informal Patent Application (PTO-152) er:	
S. Patent and Tra TO-326 (Rev		ction Summary	Part of Paper N	 No. 7

Art Unit: 2812

## **DETAILED ACTION**

1. Applicant's election without traverse of Group I, claims 21, 27-28, 31, and 36-38 in Paper No. 6 is acknowledged.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

- (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. Claims 21, 27, and 38 are rejected under 35 U.S.C. 103(a) as being unpatentable over Atchison (US Patent 6,324,481) in view of Kircsh (US Patent 6,507,933).
- 3. As for claim 21, Atchison disclosed the invention substantially as claimed, including an inspection system comprising

an inspection apparatus for detecting positions and sizes of particles or pattern defects on an object to be inspected [col. 4, lines 46-55];

an image taking apparatus for taking images of said particles or said pattern defects as detected by said inspection apparatus [col. 1, line 63 col. 2, line 15 and figure 7 elements 132, 134, and 136; col. 4, lines 46-55];

an analysis unit operatively coupled to said inspection apparatus and said image taking apparatus, said analysis unit including [col. 1, line 63 col. 2, line 15 and figure 7 elements 132, 134, and 136]; col. :

Art Unit: 2812

a storage device for storing therein inspection data produced by said inspection apparatus and position information of regions of a circuit pattern to be formed on said object [col. 4, line 46 –col. 5, line 19, especially col. 5, lines 9-10 for the storage device];

a calculation device for identifying particle and pattern defects that are correspondingly positioned in said regions, and calculating failure probabilities for said particles and said pattern defects positioned in said regions based on their sizes [col. 4, line 46 –col. 6, line 20, especially col.'s 5-6, where the specific calculations are done]; and

a selection device for selecting particles or pattern defects for calculated failure probabilities [col. 4, line 46 –col. 6, line 20, especially col.'s 5-6, where defects of interest and defect types are disclosed].

Atchison did not specifically disclose selecting particles or pattern defects whose calculated failure probabilities are greater than or equal to a predetermined threshold.

Kirsch disclosed selecting defects where failure probabilities are equal to or greater than a predetermined threshold [col. 4, lines 56-67].

It would have been obvious to one of ordinary skill in the art at the time the invention was made to combine the teachings of Atchison and Kirsch because selecting particles or pattern defects equal to or greater than a predetermined threshold value in Atchison's system would have allowed for Atchison's system to set quality control limits on defects to set acceptable limits within desired limits which would improve the production process [see Kirsch col. 4, lines 56-67].

4. As for claim 36, Atchison disclosed the invention substantially as claimed, including a method for manufacturing semiconductor devices comprising the steps of:

a fabrication step for forming circuit patterns on or over a wafer, said circuit patterns constituting a plurality of semiconductor chips [col.'s 1-2];

Art Unit: 2812

an inspection step for detecting positions and sizes of particles or pattern defects on an said wafer [col.'s 4-5];

identifying positions and sizes of those of said particles or said pattern defects located in a region of said circuit patterns that constitute one of said semiconductor chips [col.'s4-5];

a calculation step for calculating failure probabilities based on sizes of said pattern defects in said region [col. 4, line 46 –col. 6, line 20, especially col.'s 5-6, where the specific calculations are done];

an extraction step for extracting positions of said particles or said pattern defects with calculated failure probabilities [col. 4, line 64 – col. 5, line 29]; and

producing images of said particles or said pattern defects extracted at said extraction step [col. 4, line 64 – col. 5, line 29, especially col. 5, lines 14-17].

Atchison did not specifically disclose that positions of particles or defects are extracted for a calculated failure probability greater than or equal to a predefined threshold. Kirsch disclosed an equal to or greater than threshold for extracting wafers with defects [col. 4, lines 56-67].

It would have been obvious to one of ordinary skill in the art at the time the invention was made to combine the teachings of Atchison and Kirsch because extracting particles or pattern defects equal to or greater than a predetermined threshold value in Atchison's system would have allowed for Atchison's system to set quality control limits on defects to set acceptable limits within desired limits which would improve the production process [see Kirsch col. 4, lines 56-67].

5. As for claim 27, Atchison disclosed a simulation device for generating virtual defects at random positions with respect to circuit graphics obtainable from mask layout data forming said circuit pattern, and computing said failure probabilities from connection relationships of said circuit graphics and said defects [col. 5, lines 1-15, and 57-67; and col. 6, lines 1-7].

Art Unit: 2812

6. Claims 24, 28, 31, and 37-38 are rejected under 35 U.S.C. 103(a) as being unpatentable over Atchison (US Patent 6,324,481) in view of Kircsh (US Patent 6,507,933).

As for claims 24, 28, 31, and 37-38, Atchison in view of Kirsch disclosed the invention substantially as claimed, including the method and apparatus for inspecting semiconductor devices as cited in the rejections of claims 21, 27-28, and 36 above, and further disclosed said position information of said regions is generated from mask layout data of circuit blocks, and [see Atchison, as cited in the rejection of claims 21, and 36].

Atchison in view of Kirsch did not specifically disclose circuit blocks are formed as LSI chip and include memory and logic portions.

Hashimoto disclosed system LSI with logic and memory portions and mask layout data [col. 3, lines 50-54; and col. 9, lines 50-60].

It would have been obvious to one of ordinary skill in the art at the time the invention was made to combine the teachings of Atchison in view of Kirsch and Hashimoto because Atchison in view of Kirsch disclosed the inspection system and method including semiconductor IC's [see Atchison, col. 1, lines 35-45] which comprise integrated circuits such as LSI's, and Hashimoto disclosed system LSI's including logic and memory portions. The inspection of circuit blocks within system LSI's and the position information of said regions which is generated from mask layout data of circuit blocks would have allowed Atchison in view of Kirsch's inspection system to evaluate defect conditions of well known circuits such as the LSI for the manufacturing of good circuits with as little defect as possible.

7. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Stacy A Whitmore whose telephone number is (703)

Art Unit: 2812

305-0565. The examiner can normally be reached on Monday-Thursday, alternate Friday 6:30am - 4:00 pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, John Niebling can be reached on (703) 308-3325. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 308-7724 for regular communications and (703) 308-7724 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

Stacy A Whitmore
Patent Examiner
Art Unit 2812

**SAW** 

March 27, 2003

AND HE